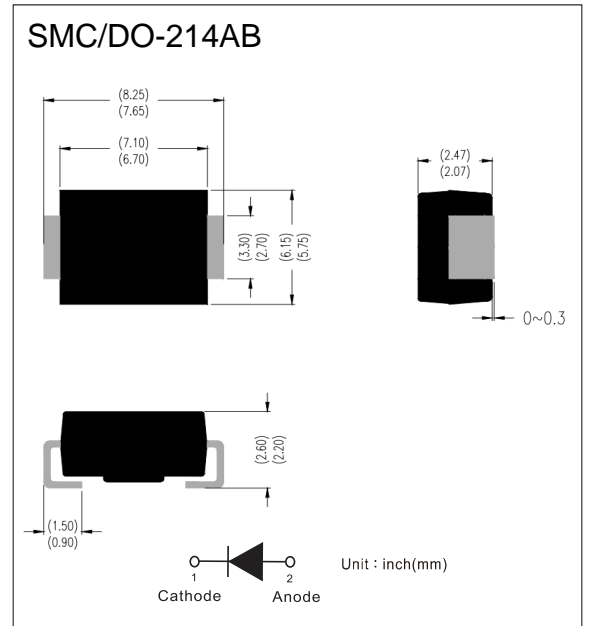


■ **Features**

- Glass passivated junction chip
- Ideal for automated placement
- Low forward voltage drop
- High surge current capability

■ **Mechanical Data**

- package: SMC/DO-214AB
- Polarity: Indicated by cathode band
- Epoxy: UL 94V-0 rate flame retardant
- Mounting Position : Any



■ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	SYMBOL	UNIT	S10A	S10B	S10D	G10G	S10J	S10K	S10M
Maximum Repetitive peak reverse voltage	$V_{RRM}$	V	50	100	200	400	600	800	1000
Maximum RMS Voltage	$V_{RMS}$	V	35	70	140	280	420	560	700
Maximum DC Blocking Voltage	$V_{DC}$	V	50	100	200	400	600	800	1000
Average Rectified Output Current @60Hz sine wave, Resistance load, TL (FIG.1)	$I_o$	A	10						
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, $T_j=25^{\circ}\text{C}$	$I_{FSM}$	A	200						
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, $T_j=25^{\circ}\text{C}$			400						
Current squared time @1ms≤t≤8.3ms $T_j=25^{\circ}\text{C}$ , Rating of per diode	$I^2t$	$\text{A}^2\text{s}$	166						
Typical junction capacitance @Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	$C_j$	pF	55						
Storage Temperature	$T_{stg}$	$^{\circ}\text{C}$	-55 ~ +150						
Junction Temperature	$T_j$	$^{\circ}\text{C}$	-55 ~ +150						



■ Thermal Performance( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	SYMBOL	UNIT	S10A	S10B	S10D	S10G	S10J	S10K	S10M		
Typical Thermal resistance	R $\theta$ J-A(1)	$^{\circ}\text{C}/\text{W}$	50								
	R $\theta$ J-L(1)		10								
	R $\theta$ J-C(1)		8								

Note(1)

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6" x 0.6" (16 mm x 16 mm) copper pad areas

■ Electrical Specifications( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	S10A	S10B	S10D	S10G	S10J	S10K	S10M	
Maximum instantaneous forward voltage drop per diode	V <sub>F</sub>	V	I <sub>FM</sub> =10A	1.1							
Maximum DC reverse current at rated DC blocking voltage per diode	I <sub>R</sub>	$\mu\text{A}$	T <sub>j</sub> =25 $^{\circ}\text{C}$	5							
			T <sub>j</sub> =125 $^{\circ}\text{C}$	100							



■ Characteristics Curves( $T_A=25^\circ\text{C}$  unless otherwise noted)

FIG.1:  $I_o$ -TL Curve

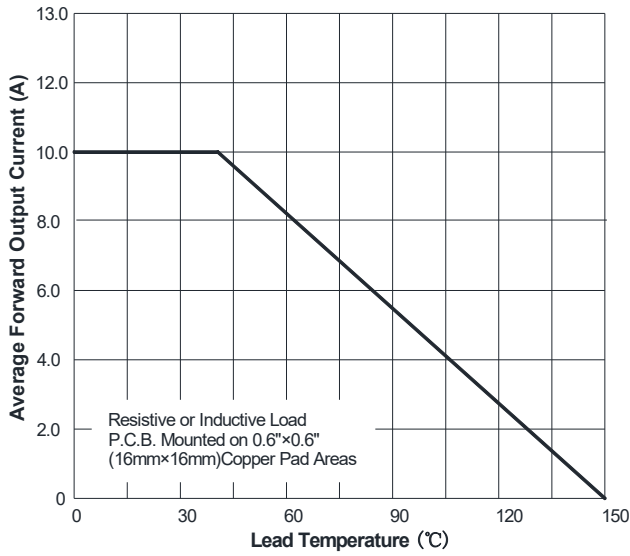


FIG.2: Forward Surge Current Capability

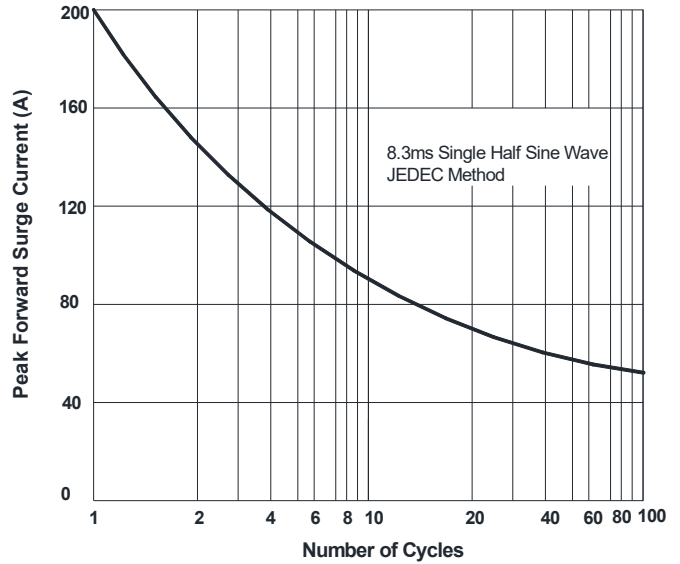


FIG.3: Typical Forward Voltage

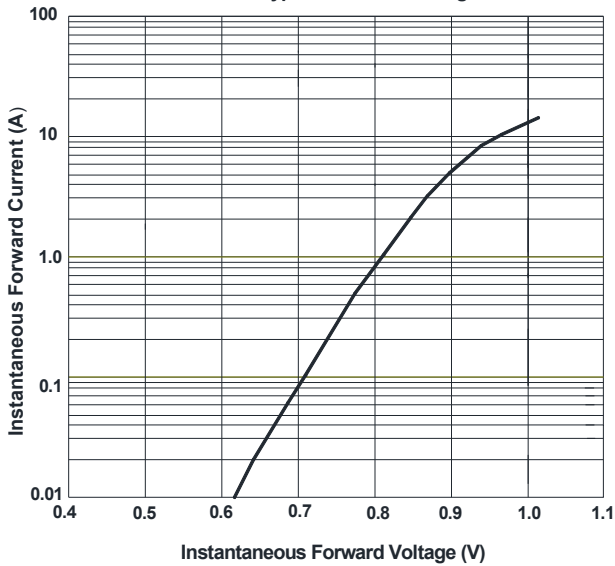
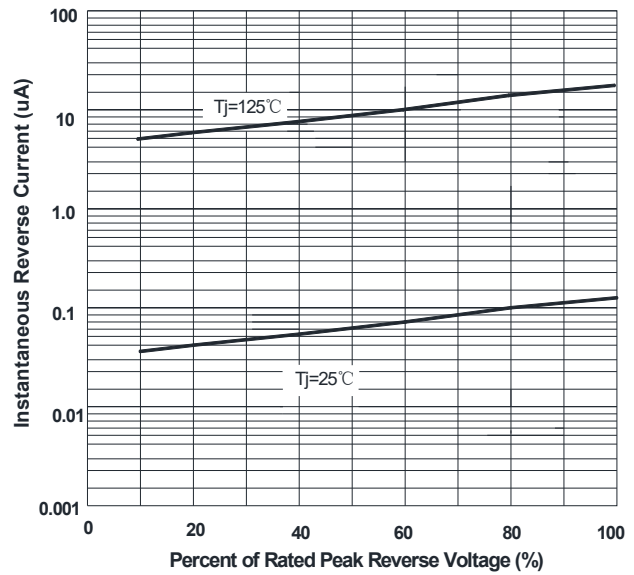


FIG.4: Typical Reverse Characteristics



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